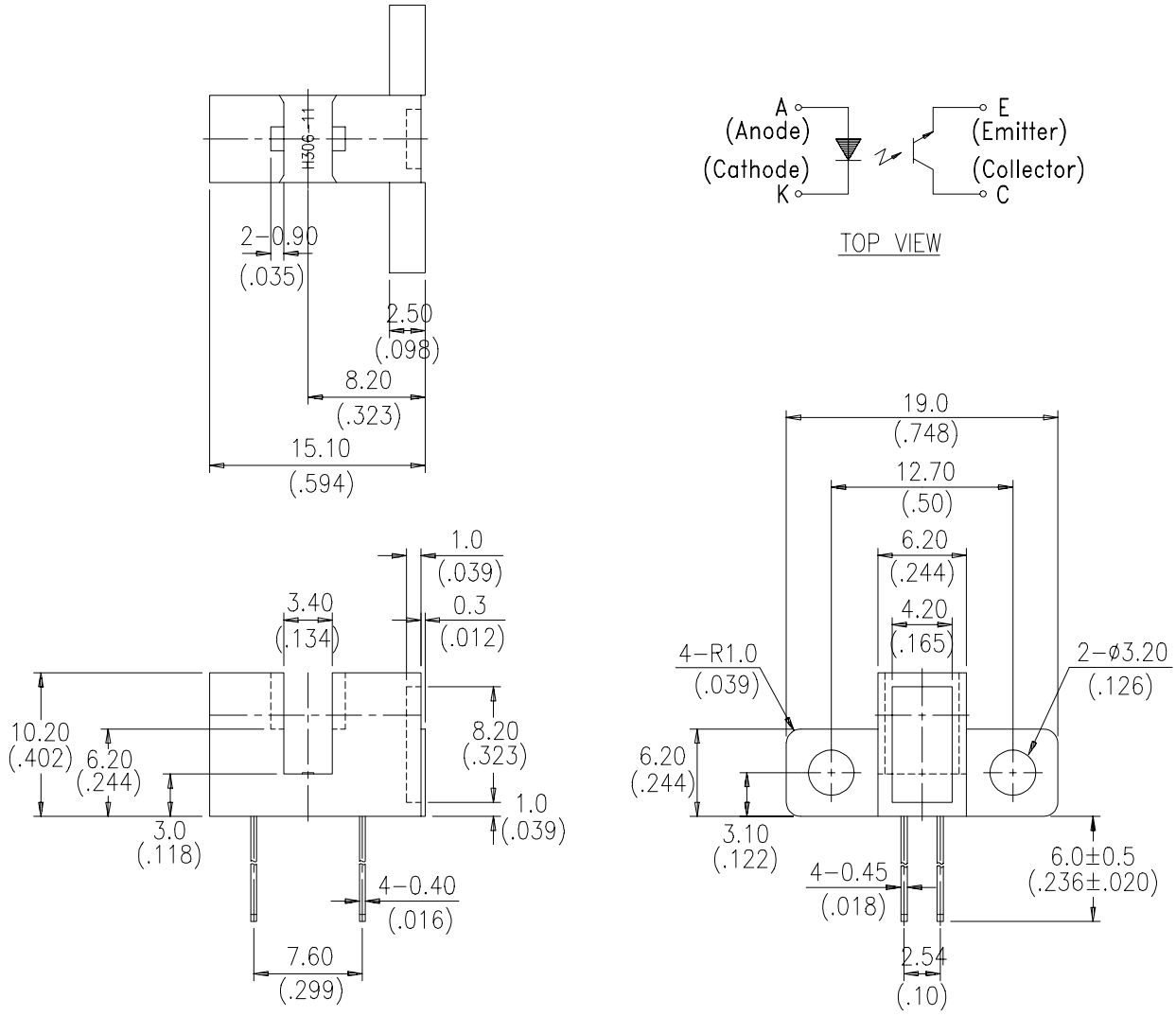
FEATURES

* NON-CONTACT SWITCHING.
* FOR DIRECT PC BOARD OR DUAL-IN-LINE SOCKET MOUNTING.
* FAST SWITCHING SPEED.

PACKAGE DIMENSIONS



NOTES:
1. All dimensions are in millimeters (inches).
2. Tolerance is ±0.25mm(.010") unless otherwise noted.

ABSOLUTE MAXIMUM RATINGS AT TA=25℃

PARAMETER	MAXIMUM RATING	UNIT
IR Diode Continuous Forward Current	50	mA
IR Diode Reverse Voltage	5	V
Transistor Collector Currant	20	mA
Transistor Power Dissipation	75	mW
IR Diode Peak Power Currant (Pulse Wide = 1 μS, 300 pps)	1	A
Diode Power Dissipation	60	mW
Phototransistor Collector-Emitter Voltage	30	V
Phototransistor Emitter-Collector Voltage	5	V
Operating Temperature Range	-25℃ to + 85℃	
Storage Temperature Range	-55℃ to + 100℃	
Lead Soldering Temperature [1.6mm(.063") From Body]	260℃ for 5 Seconds	

ELECTRICAL OPTICAL CHARACTERISTICS AT TA=25℃

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
INPUT LED						
Forward Voltage	VF		1.2	1.6	V	IF = 20mA
Reverse Current	IR			100	μA	VR=5V
OUTPUT PHOTOTRANSISTOR						
Collector-Emitter Breakdown Voltage	V(BR)CEO	30			V	IC=1mA
Emitter-Collector Breakdown Voltage	V(BR)CEO	5			V	IE=0.1mA
Collector-Emitter Dark Current	ICEO			100	nA	VCE=10V
COUPLER						
Collector-Emitter Saturation Voltage	VCE(SAT)			0.4	V	IC=0.2mA IF=20mA
On State Collector Current	Ic(ON)	1		28	mA	VCE=5V IF=20mA
Rise Time	Tr		4		μS	Ic=1mA Rc=1KΩ
Fall Time	Tr		12			

TYPICAL ELECTRICAL / OPTICAL CHARACTERISTICS CURVES

(25℃ Ambient Temperature Unless Otherwise Noted)

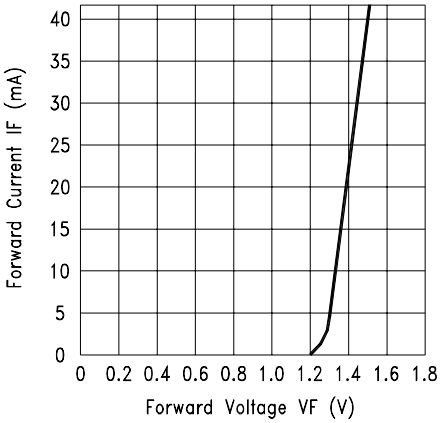


Fig.1 FORWARD CURRENT VS. FORWARD VOLTAGE

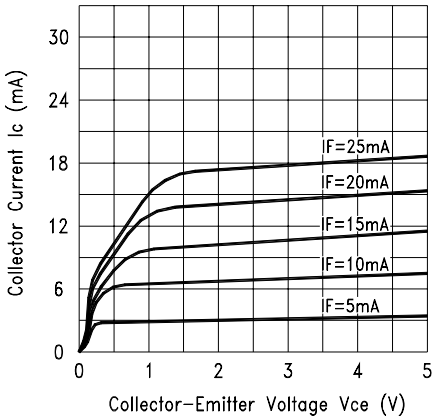


Fig.2 COLLECTOR CURRENT VS. COLLECTOR VOLTAGE

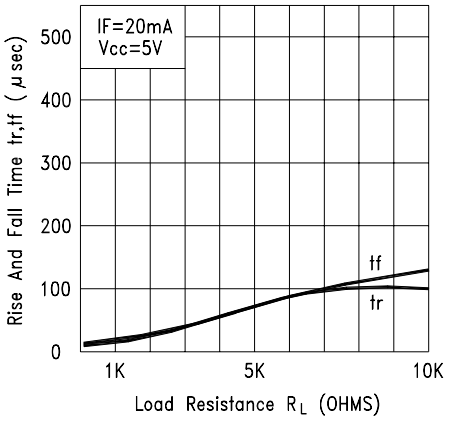


Fig.3 RISE AND FALL TIME VS. LOAD RESISTANCE

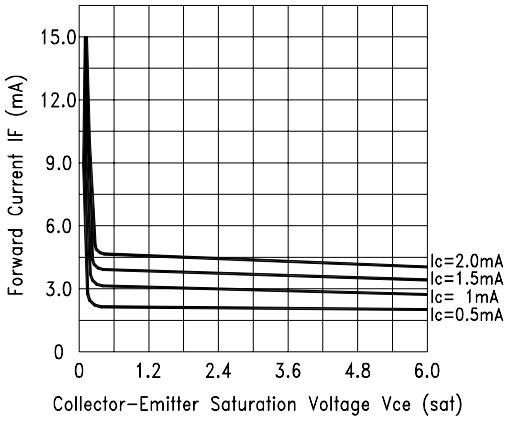


Fig.4 FORWARD CURRENT VS. Collector-Emitter Saturation Voltage